Pb Free Product



NCE0117

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0117 uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. It can be used in a wide variety of applications.

General Features

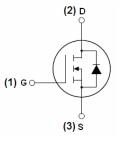
- V_{DS} =100V,I_D =17A
 - $R_{DS(ON)} < 70 \text{m}\Omega$ @ $V_{GS}=10V$ (Typ:56m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



Schematic diagram



Marking and pin assignment



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0117	NCE0117	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	17	А
Drain Current-Continuous(T _C =100°C)	I _D (100°C)	12	Α
Pulsed Drain Current	I _{DM}	60	Α
Maximum Power Dissipation	P _D	55	W
Single pulse avalanche energy (Note 5)	E _{AS}	250	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C



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NCE0117

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	2.27	°C/W	1
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	56	70	mΩ
Forward Transconductance	g FS	V _{DS} =50V,I _D =9A	12	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	1350	-	PF
Output Capacitance	C _{oss}	V_{DS} =25V, V_{GS} =0V,	-	240	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	180	-	PF
Switching Characteristics (Note 4)			1			
Turn-on Delay Time	t _{d(on)}		-	13.8	-	nS
Turn-on Rise Time	t _r	V_{DD} =30 V , I_D =2 A , R_L =15 Ω	-	9.3	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10V, R_{G} =2.5 Ω	-	43.8	-	nS
Turn-Off Fall Time	t _f		-	11.4	-	nS
Total Gate Charge	Q_g	\/ 00\/ L 0A	-	31		nC
Gate-Source Charge	Q_{gs}	V _{DS} =30V,I _D =3A,	-	6.4	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	9.4	-	nC
Drain-Source Diode Characteristics	•		•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	17	Α
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

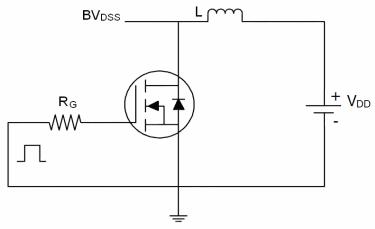
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
- **3.** Pulse Test: Pulse Width $\leq 300 \,\mu\,\mathrm{s}$, Duty Cycle $\leq 2\%$.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition : Tj=25 $^{\circ}$ C,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω



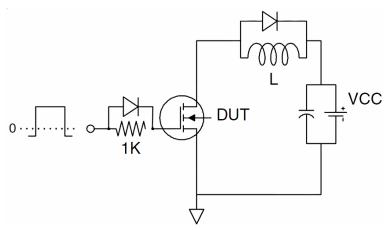
NCE0117

Test Circuit

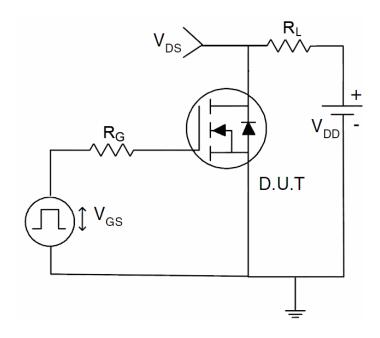
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







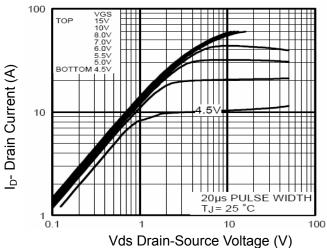


Figure 1 Output Characteristics

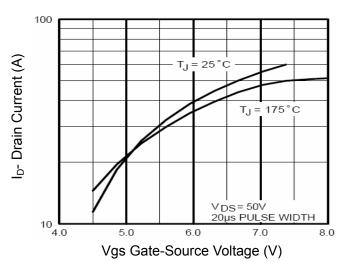


Figure 2 Transfer Characteristics

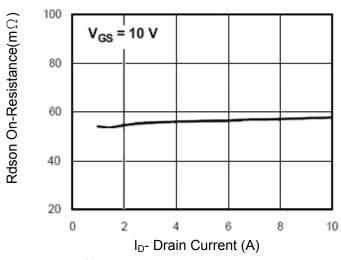


Figure 3 Rdson- Drain Current

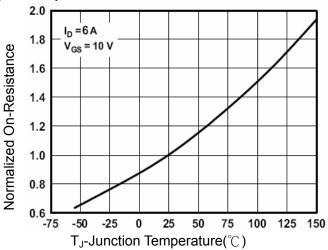


Figure 4 Rdson-JunctionTemperature

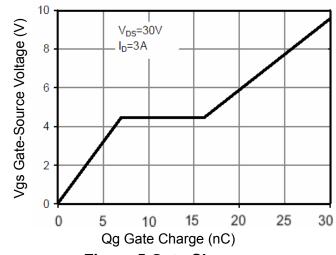


Figure 5 Gate Charge

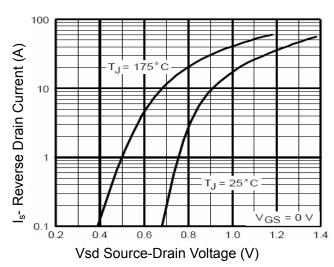


Figure 6 Source- Drain Diode Forward



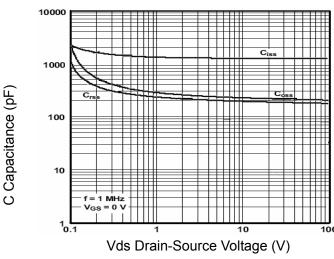


Figure 7 Capacitance vs Vds

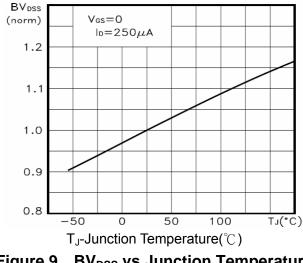


Figure 9 **BV_{DSS} vs Junction Temperature**

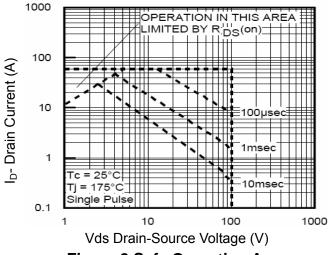


Figure 8 Safe Operation Area

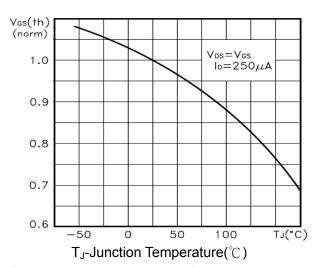


Figure 10 V_{GS(th)} vs Junction Temperature

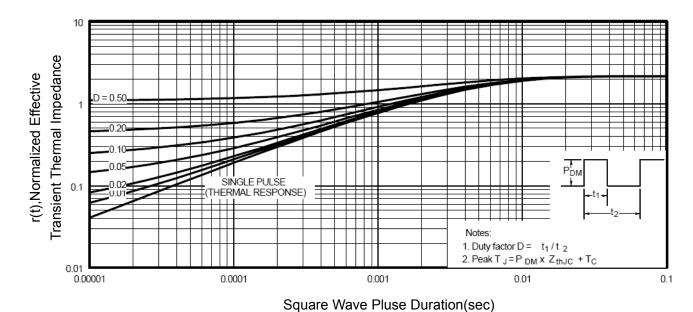
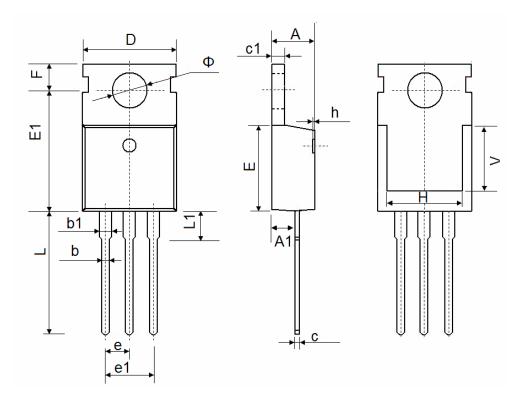


Figure 11 Normalized Maximum Transient Thermal Impedance

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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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